Hex Inverter

(Unbuffered)

The MC74VHCU04 is an advanced high speed CMOS unbuffered inverter fabricated with silicon gate CMOS technology. It achieves high speed operation similar to equivalent Bipolar Schottky TTL while maintaining CMOS low power dissipation.

The inputs tolerate voltages up to 7.0 V, allowing the interface of 5.0 V systems to 3.0 V systems.

Features

- High Speed: $t_{PD} = 3.5 \text{ ns}$ (Typ) at $V_{CC} = 5.0 \text{ V}$
- Low Power Dissipation: $I_{CC} = 2 \mu A$ (Max) at $T_A = 25$ °C
- High Noise Immunity: $V_{NIH} = V_{NIL} = 10\% V_{CC}$ (Min.)
- Power Down Protection Provided on Inputs
- Balanced Propagation Delays
- Designed for 2.0 V to 5.5 V Operating Range
- Pin and Function Compatible with Other Standard Logic Families
 Latchup Performance Exceeds 300 m A
- ESD Performance:

Human Body Model > 2000 V; Machine Model > 200 V

- Chip Complexity: 12 FETs or 3 Equivalent Gates
- Pb-Free Packages are Available*

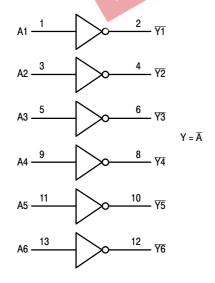


Figure 1. Logic Diagram



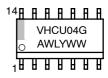
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MARKING **DIAGRAMS**



SOIC-14 **D SUFFIX CASE 751A**



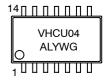


TSSOP-14 DT SUFFIX **CASE 948G**





SOEIAJ-14 **M SUFFIX CASE 965**



= Assembly Location = Wafer Lot WI I

Y, YY = Year WW, W = Work Week

G or ■ = Pb-Free Package

(Note: Microdot may be in either location)

FUNCTION TABLE

Inputs	Outputs
Α	Y
L	Н
н	L

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 4 of this data sheet.

^{*}For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

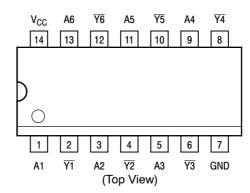


Figure 2. Pinout: 14-Lead Packages

MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V _{CC}	DC Supply Voltage	-0.5 to + 7.0	V
V _{in}	DC Input Voltage	-0.5 to + 7.0	V
V _{out}	DC Output Voltage	-0.5 to V _{CC} + 0.5	V
I _{IK}	Input Diode Current	-20	mA
I _{OK}	Output Diode Current	±[2 0	mA
l _{out}	DC Output Current, per Pin	± [25	mA
Icc	DC Supply Current, V _{CC} and GND Pins	±[5 0	mA
P _D	Power Dissipation in Still Air, SOIC Packages†	500	mW
	TSSOP Package†	450	
T _{stg}	Storage Temperature	- 65 to + 150	°C

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

†Derating — SOIC Packages: – 7 mW/°C from 65° to 125°C TSSOP Package: – 6.1 mW/°C from 65° to 125°C

This device contains protection circuitry to guard against damage due to high static voltages or electric fields. However, precautions must be taken to avoid applications of any voltage higher than maximum rated voltages to this high–impedance circuit. For proper operation, V_{in} and V_{out} should be constrained to the range GND \leq (V_{in} or V_{out}) \leq V_{CC} .

Unused inputs must always be tied to an appropriate logic voltage level (e.g., either GND or V_{CC}). Unused outputs must be left open.

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Min	Max	Unit
V _{CC}	DC Supply Voltage	2.0	5.5	V
V _{in}	DC Input Voltage	0	5.5	V
V _{out}	DC Output Voltage	0	V _{CC}	V
T _A	Operating Temperature	-40	+ 85	°C

DC ELECTRICAL CHARACTERISTICS

			V _{cc}		T _A = 25°C		$T_A = -40$) to 85°C	
Symbol	Parameter	Test Conditions	V	Min	Тур	Max	Min	Max	Unit
V _{IH}	Minimum High-Level Input Voltage		2.0 3.0 to 5.5	1.70 V _{CC} x 0.8			1.70 V _{CC} x 0.8		V
V _{IL}	Maximum Low-Level Input Voltage		2.0 3.0 to 5.5			0.30 V _{CC} x 0.2		0.30 V _{CC} x 0.2	V
V _{OH}	Minimum High-Level Output Voltage	$V_{in} = V_{IL}$ $I_{OH} = -50\mu A$	2.0 3.0 4.5	1.8 2.7 4.0	2.0 3.0 4.5		1.8 2.7 4.0		V
		V _{in} = GND I _{OH} = -4mA I _{OH} = -8mA	3.0 4.5	2.58 3.94			2.48 3.80		
V _{OL}	Maximum Low-Level Output Voltage	$V_{in} = V_{IH}$ $I_{OL} = 50\mu A$	2.0 3.0 4.5		0.0 0.0 0.0	0.2 0.3 0.5		0.2 0.3 0.5	V
		$V_{in} = V_{CC}$ $I_{OL} = 4mA$ $I_{OL} = 8mA$	3.0 4.5			0.36 0.36		0.44 0.44	
l _{in}	Maximum Input Leakage Current	V _{in} = 5.5 or GND	0 to 5.5		.80	±[0.1		±[1.0	μΑ
I _{CC}	Maximum Quiescent Supply Current	$V_{in} = V_{CC}$ or GND	5.5	4 %	30	2.0		20.0	μΑ

AC ELECTRICAL CHARACTERISTICS (Input t_r = t_f = 3.0ns)

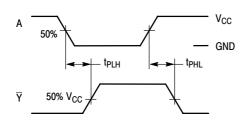
			C	T _A = 25°C		$T_A = -40$	to 85°C	
Symbol	Parameter	Test Conditions	Min	Тур	Max	Min	Max	Unit
t _{PLH} , t _{PHL}	Maximum Propagation Delay, A or B to \overline{Y}	$\begin{array}{c} V_{CC} = 3.3 \pm 0.3 V & C_L = 15 pF \\ C_L = 50 pF \end{array}$		5.0 7.5	8.9 11.4	1.0 1.0	10.5 13.0	ns
	13	$V_{CC} = 5.0 \pm 0.5V \qquad \begin{array}{c} C_L = 15 pF \\ C_L = 50 pF \end{array}$		3.5 5.0	5.5 7.0	1.0 1.0	6.5 8.0	
C _{in}	Maximum Input Capacitance			5	10		10	pF

		Typical @ 25°C, V _{CC} = 5.0V	
C _{PD}	Power Dissipation Capacitance (Per Inverter) (Note 1)	9	pF

^{1.} C_{PD} is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load. Average operating current can be obtained by the equation: I_{CC(OPR)} = C_{PD} • V_{CC} • f_{in} + I_{CC}/6 (per buffer). C_{PD} is used to determine the no–load dynamic power consumption; P_D = C_{PD} • V_{CC}² • f_{in} + I_{CC} • V_{CC}.

NOISE CHARACTERISTICS (Input t_r = t_f = 3.0ns, C_L = 50pF, V_{CC} = 5.0V)

		T _A = 25°C		
Symbol	Characteristic	Тур	Max	Unit
V _{OLP}	Quiet Output Maximum Dynamic V _{OL}	0.5	0.8	V
V _{OLV}	Quiet Output Minimum Dynamic V _{OL}	-0.5	-0.8	V
V _{IHD}	Minimum High Level Dynamic Input Voltage		4.0	V
V _{ILD}	Maximum Low Level Dynamic Input Voltage		1.0	V

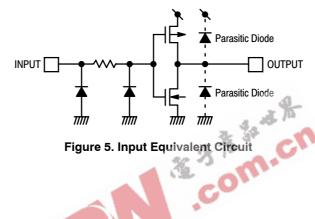


TEST POINT OUTPUT DEVICE UNDER **TEST**

*Includes all probe and jig capacitance

Figure 3. Switching Waveforms

Figure 4. Test Circuit



ORDERING INFORMATION

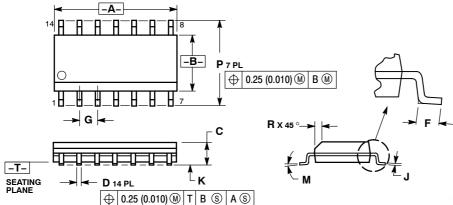
Device	Package	Shipping [†]
MC74VHCU04DR2	SOIC-14	2500 Tape & Reel
MC74VHCU04DR2G	SOIC-14 (Pb-Free)	2500 Tape & Reel
MC74VHCU04DTR2	TSSOP-14*	2500 Tape & Reel
MC74VHCU04DTR2G	TSSOP-14*	2500 Tape & Reel
MC74VHCU04MEL	SOEIAJ-14	2000 Tape & Reel
MC74VHCU04MELG	SOEIAJ-14 (Pb-Free)	2000 Tape & Reel

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

^{*}This package is inherently Pb-Free.

PACKAGE DIMENSIONS

SOIC-14 **D SUFFIX** CASE 751A-03 ISSUE G



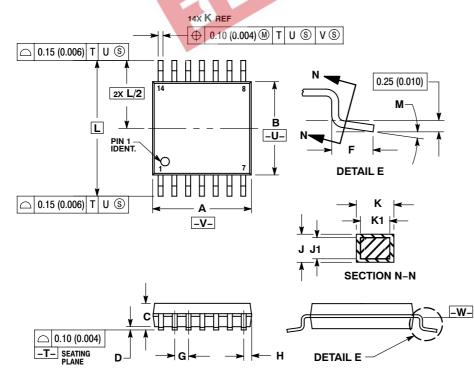
NOTES:

- 1. DIMENSIONING AND TOLERANCING PER
- ANSI Y14.5M, 1982. 2. CONTROLLING DIMENSION: MILLIMETER. DIMENSIONS A AND B DO NOT INCLUDE MOLD PROTRUSION.
 MAXIMUM MOLD PROTRUSION 0.15 (0.006)
- 5. DIMENSION D DOES NOT INCLUDE

CONDITION.	
DIMENSION AT MAXIMUM MATERIAL	
(0.005) TOTAL IN EXCESS OF THE D	
DAMBAR PROTRUSION SHALL BE 0.12	27
DAMBAR PROTRUSION. ALLOWABLE	

	MILLIMETERS		INC	HES
DIM	MIN	MAX	MIN	MAX
Α	8.55	8.75	0.337	0.344
В	3.80	4.00	0.150	0.157
O	1.35	1.75	0.054	0.068
D	0.35	0.49	0.014	0.019
E	0.40	1.25	0.016	0.049
G	1.27	BSC	0.050	BSC
J	0.19	0.25	0.008	0.009
K	0.10	0.25	0.004	0.009
M	0 °	7°	0°	7°
∭P	5.80	6.20	0.228	0.244
R	0.25	0.50	0.010	0.019





- NOTES:

 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
 2. CONTROLLING DIMENSION: MILLIMETER.
 3. DIMENSION A DOES NOT INCLUDE MOLD FLASH, PROTRUSIONS OR GATE BURRS. MOLD FLASH OR GATE BURRS SHALL NOT EXCEED A 15 (000) DEP. SIDE

 - MOLD FLASH OR GATE BURRS SHALL NOT EXCEED 0.15 (0.006) PER SIDE.

 4. DIMENSION B DOES NOT INCLUDE INTERLEAD FLASH OR PROTRUSION. INTERLEAD FLASH OR PROTRUSION SHALL NOT EXCEED 0.25 (0.010) PER SIDE.

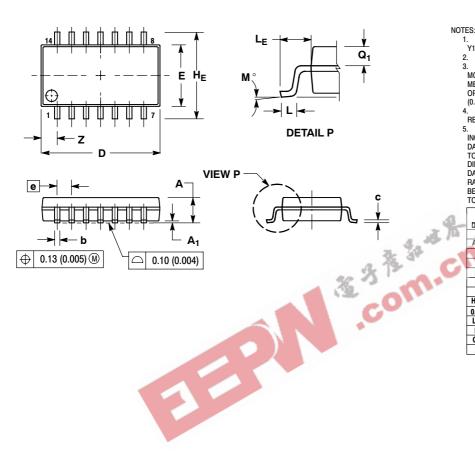
 5. DIMENSION K DOES NOT INCLUDE DAMBAR PROTRUSION ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08 (0.003) TOTAL IN EXCESS OF THE K DIMENSION AT MAXIMUM MATERIAL CONDITION.

 6. TERMINAL NUMBERS ARE SHOWN FOR
 - 6. TERMINAL NUMBERS ARE SHOWN FOR REFERENCE ONLY. 7. DIMENSION A AND B ARE TO BE DETERMINED AT DATUM PLANE -W-.

	MILLIN	IETERS	INC	HES
DIM	MIN	MAX	MIN	MAX
Α	4.90	5.10	0.193	0.200
В	4.30	4.50	0.169	0.177
С		1.20		0.047
D	0.05	0.15	0.002	0.006
F	0.50	0.75	0.020	0.030
G	0.65	BSC	0.026	BSC
Н	0.50	0.60	0.020	0.024
J	0.09	0.20	0.004	0.008
J1	0.09	0.16	0.004	0.006
K	0.19	0.30	0.007	0.012
K1	0.19	0.25	0.007	0.010
L	6.40	BSC	0.252	BSC
М	0 °	8°	0 °	8 °

PACKAGE DIMENSIONS

SOEIAJ-14 **M SUFFIX** CASE 965-01 **ISSUE A**



NOTES:

- 1. DIMENU. Y14.5M, 1982. DIMENSIONING AND TOLERANCING PER ANSI
- CONTROLLING DIMENSION: MILLIMETER
- B. DIMENSIONS D AND E DO NOT INCLUDE
 MOLD FLASH OR PROTRUSIONS AND ARE MEASURED AT THE PARTING LINE. MOLD FLASH OR PROTRUSIONS SHALL NOT EXCEED 0.15 (0.006) PER SIDE
- TERMINAL NUMBERS ARE SHOWN FOR REFERENCE ONLY.
- . THE LEAD WIDTH DIMENSION (b) DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08 (0.003) TOTAL IN EXCESS OF THE LEAD WIDTH
 DIMENSION AT MAXIMUM MATERIAL CONDITION. DAMBAR CANNOT BE LOCATED ON THE LOWER RADIUS OR THE FOOT. MINIMUM SPACE BETWEEN PROTRUSIONS AND ADJACENT LEAD TO BE 0.46 (0.018).

	MILLIMETERS		RS INCHES		
DIM	MIN	MAX	MIN	MAX	
Α		2.05		0.081	
A ₁	0.05	0.20	0.002	0.008	
b	0.35	0.50	0.014	0.020	
С	0.10	0.20	0.004	0.008	
D	9.90	10.50	0.390	0.413	
Е	5.10	5.45	0.201	0.215	
е	1.27	BSC	0.050 BSC		
HE	7.40	8.20	0.291	0.323	
0.50	0.50	0.85	0.020	0.033	
LE	1.10	1.50	0.043	0.059	
M	0 °	10 °	0 °	10°	
Q_1	0.70	0.90	0.028	0.035	
Z		1.42		0.056	

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